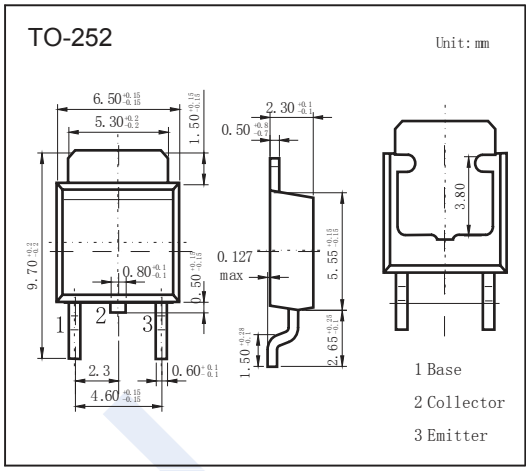
PNP Transistors

2SB928A



■ Features

- High collector-emitter voltage (Base open) V_{CEO}
- High collector power dissipation P_C
- Complementary to 2SD1250A

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-200	V
Collector - Emitter Voltage	V_{CEO}	-180	
Emitter - Base Voltage	V_{EBO}	-6	
Collector Current - Continuous	I_C	-2	A
Collector current - Pulse	I_{CP}	-3	
Collector Power Dissipation Ta = 25°C	P_C	30	W
		1.3	
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -500 μA, I_E=0	-200			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -5 mA, I_B=0	-180			
Emitter - base breakdown voltage	V_{EBO}	I_E= -500 μ A, I_C=0	-6			
Collector-base cut-off current	I_{CBO}	V_{CB}= -200V , I_E=0			-50	uA
Emitter cut-off current	I_{EBO}	V_{EB}= -4V , I_C=0			-50	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500 mA, I_B=-50mA			-1	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-500 mA, I_B=-50mA			-1.2	
Base - emitter voltage	V_{BE}	V_{CE}= -10V, I_C= -400mA			-1	
DC current gain	$h_{FE(1)}$	V_{CE}= -10V, I_C= -150mA	60		240	
	$h_{FE(2)}$	V_{CE}= -10V, I_C= -400mA	50			
Transition frequency	f_T	V_{CE}= -10V, I_C= -500mA,f=10MHz		40		MHz

■ Classification of $h_{fe(1)}$

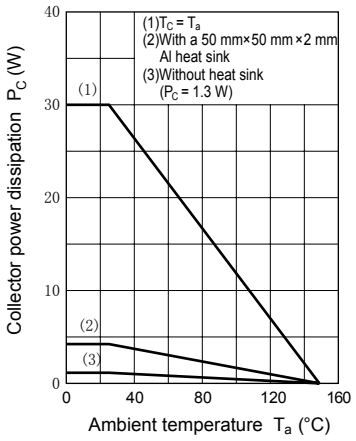
Type	2SB928A-Q	2SB928A-P
Range	60-140	100-240

PNP Transistors

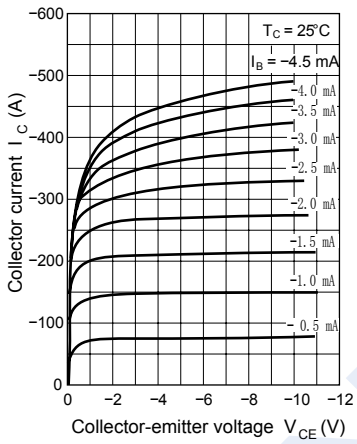
2SB928A

■ Typical Characterisitics

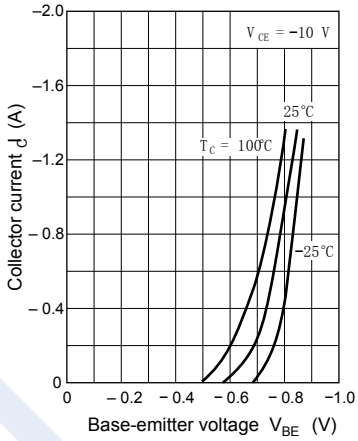
P_C – T_a



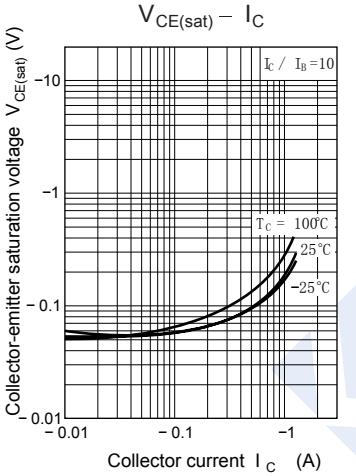
I_C – V_{CE}



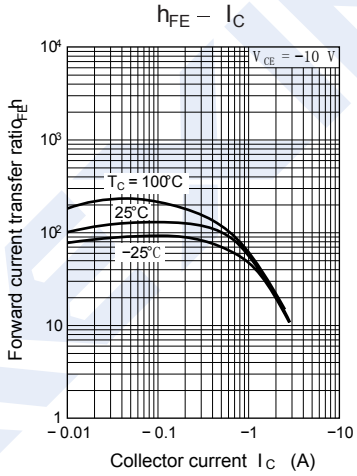
I_C – V_{BE}



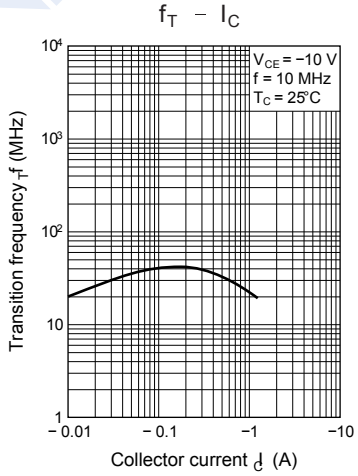
$V_{CE(sat)}$ – I_C



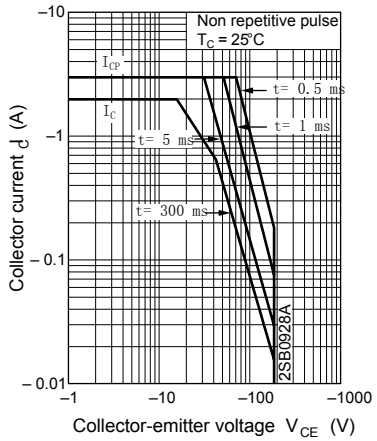
h_{FE} – I_C



f_T – I_C



Safe operation area



R_{th} – t